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# 2SK3080

Silicon N Channel MOS FET  
High Speed Power Switching

# HITACHI

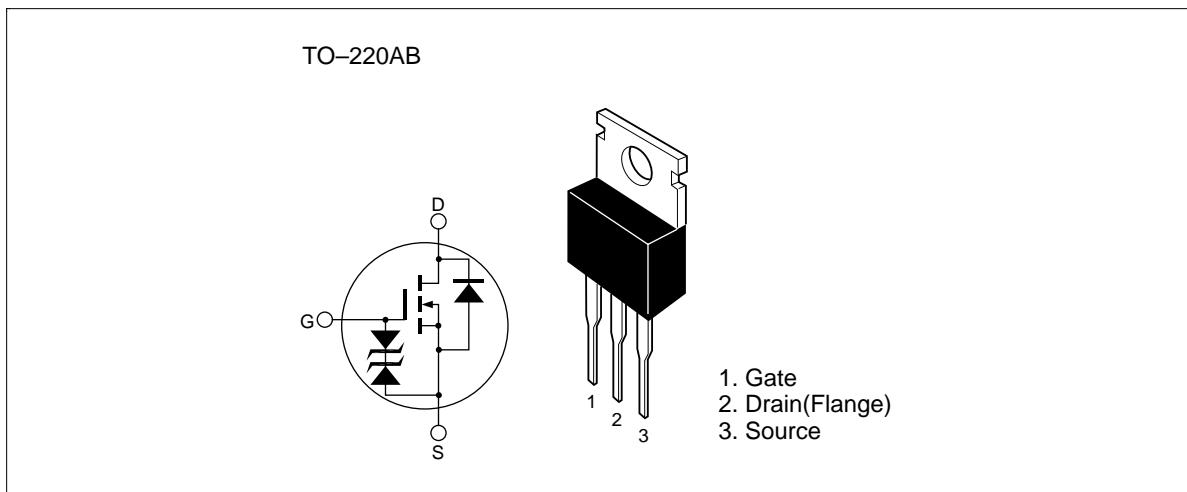
ADE-208-635A (Z)  
2nd. Edition  
May 1998

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## Features

- Low on-resistance  
 $R_{DS(on)} = 20 \text{ m}\Omega$  typ. ( $V_{GS} = 10\text{V}$ ,  $I_D = 15 \text{ A}$ )
- 4V gate drive devices.
- High speed switching

## Outline



## 2SK3080

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	30	V
Gate to source voltage	$V_{GSS}$	±20	V
Drain current	$I_D$	30	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	120	A
Body-drain diode reverse drain current	$I_{DR}$	30	A
Channel dissipation	$P_{ch}$ <sup>Note2</sup>	50	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

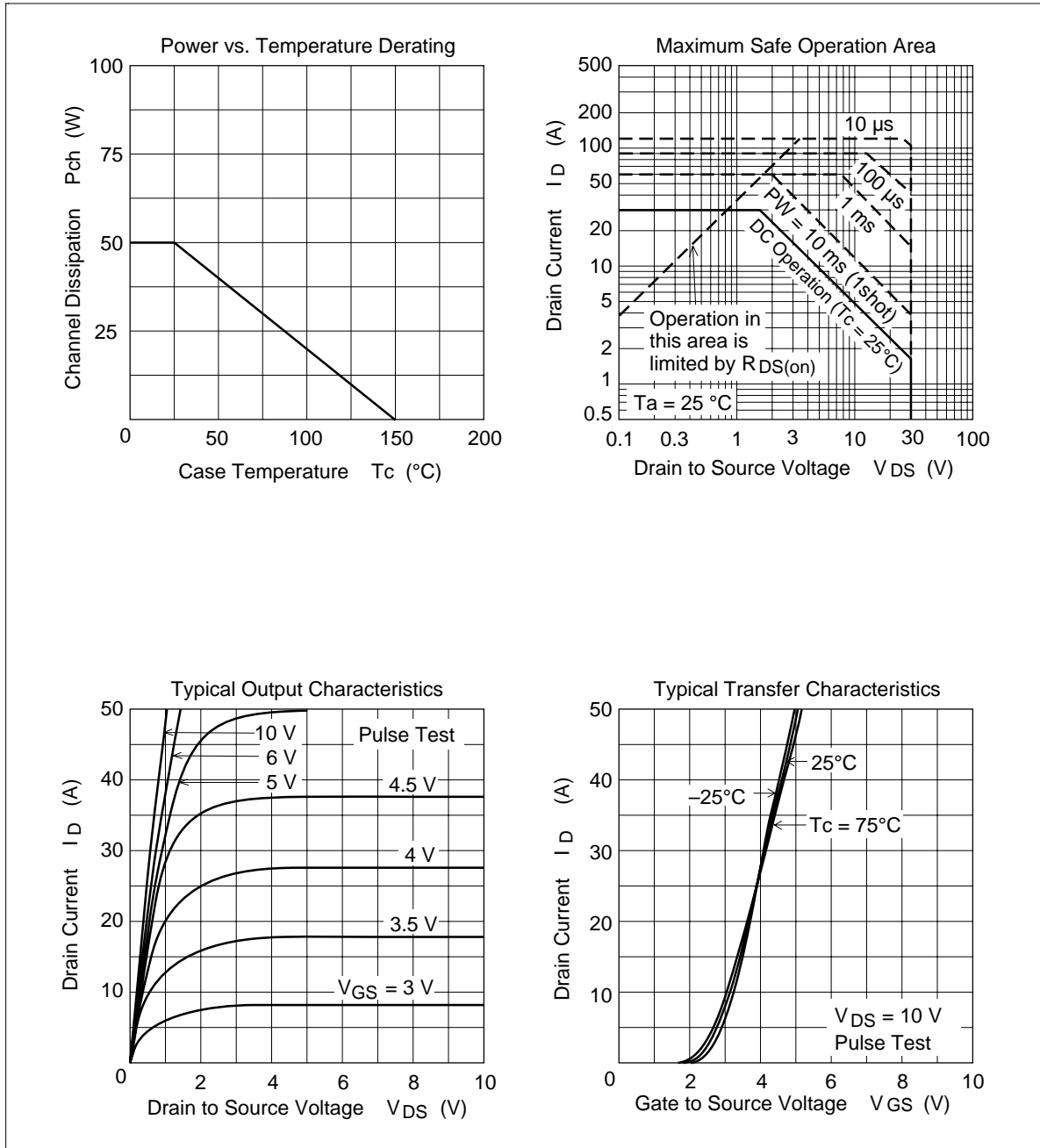
Note: 1.  $PW \leq 10\mu s$ , duty cycle  $\leq 1\%$   
 2. Value at  $T_c = 25^\circ C$

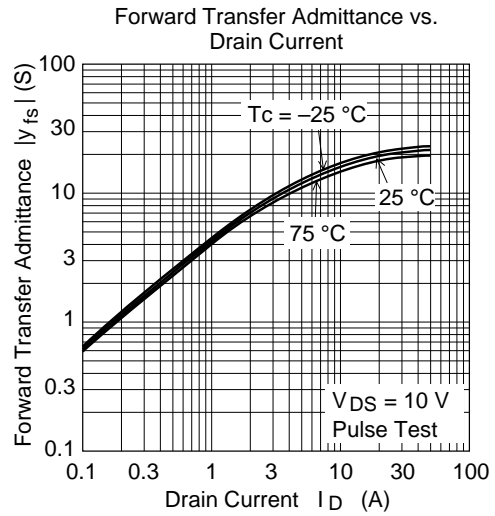
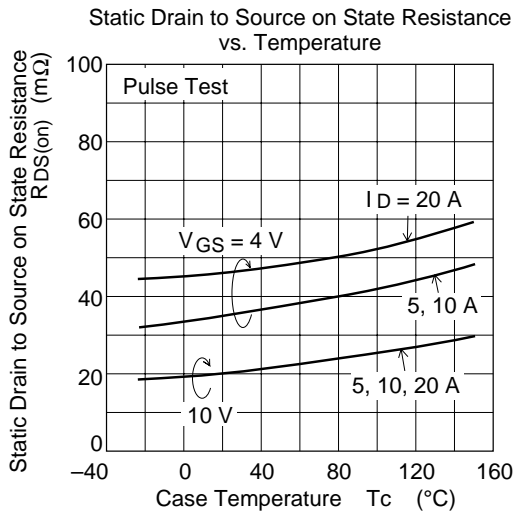
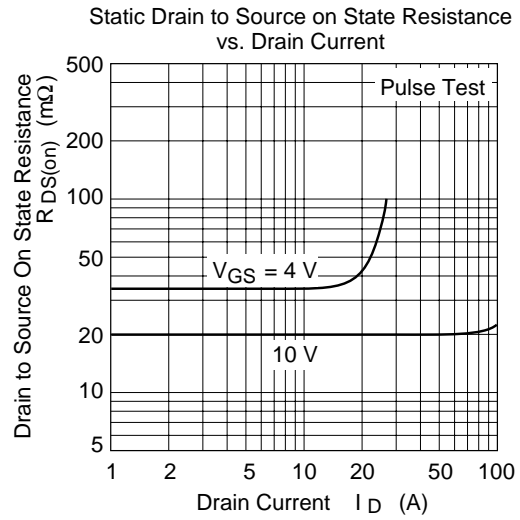
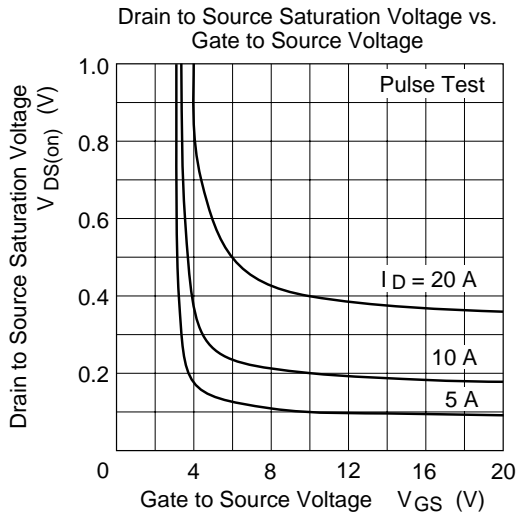
### Electrical Characteristics (Ta = 25°C)

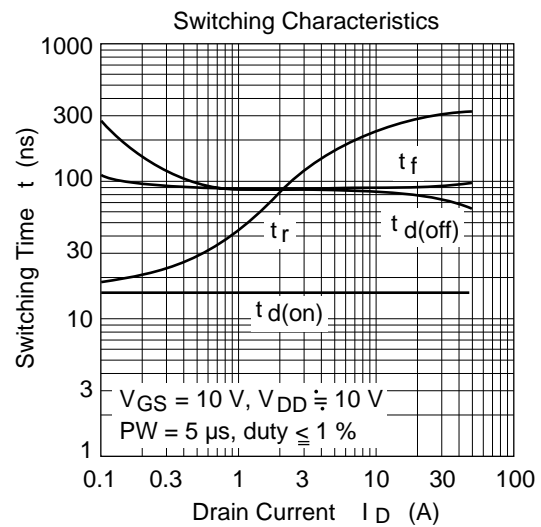
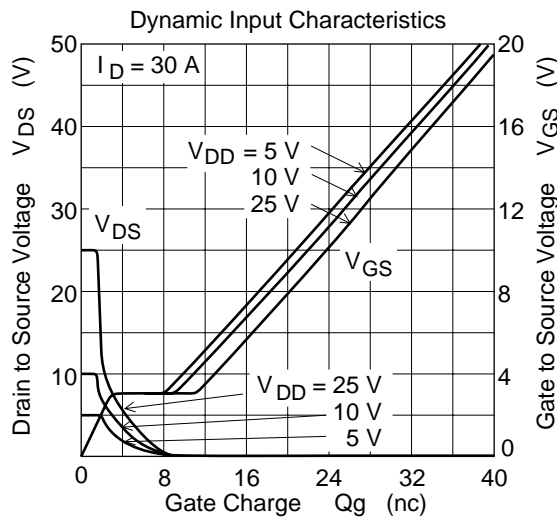
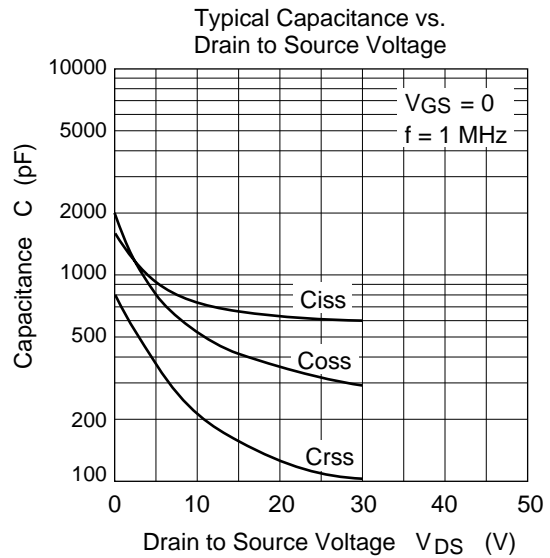
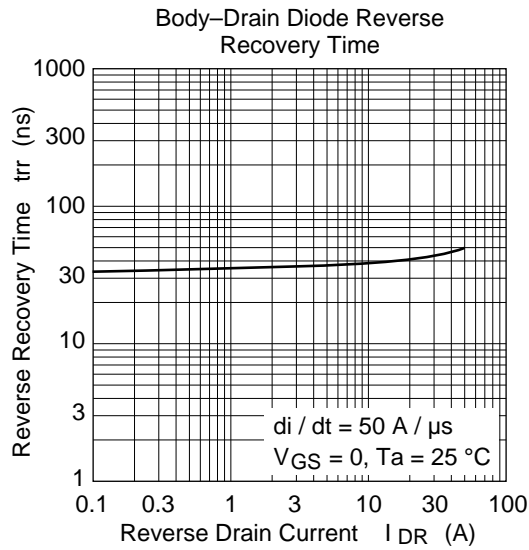
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10mA, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu A, V_{DS} = 0$
Zero gate voltage drain current	$I_{DSS}$	—	—	10	μA	$V_{DS} = 30V, V_{GS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1mA, V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	20	28	mΩ	$I_D = 15A, V_{GS} = 10V$ <sup>Note3</sup>
Static drain to source on state resistance	$R_{DS(on)}$	—	35	50	mΩ	$I_D = 15A, V_{GS} = 4V$ <sup>Note3</sup>
Forward transfer admittance	$ y_{fs} $	12	18	—	S	$I_D = 15A, V_{DS} = 10V$ <sup>Note3</sup>
Input capacitance	$C_{iss}$	—	750	—	pF	$V_{DS} = 10V$
Output capacitance	$C_{oss}$	—	520	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	$C_{rss}$	—	210	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	16	—	ns	$V_{GS} = 10V, I_D = 15A$
Rise time	$t_r$	—	260	—	ns	$R_L = 0.67\Omega$
Turn-off delay time	$t_{d(off)}$	—	85	—	ns	
Fall time	$t_f$	—	90	—	ns	
Body-drain diode forward voltage	$V_{DF}$	—	1.0	—	V	$I_F = 30A, V_{GS} = 0$
Body-drain diode reverse recovery time	$t_{rr}$	—	45	—	ns	$I_F = 30A, V_{GS} = 0$ $diF/dt = 50A/\mu s$

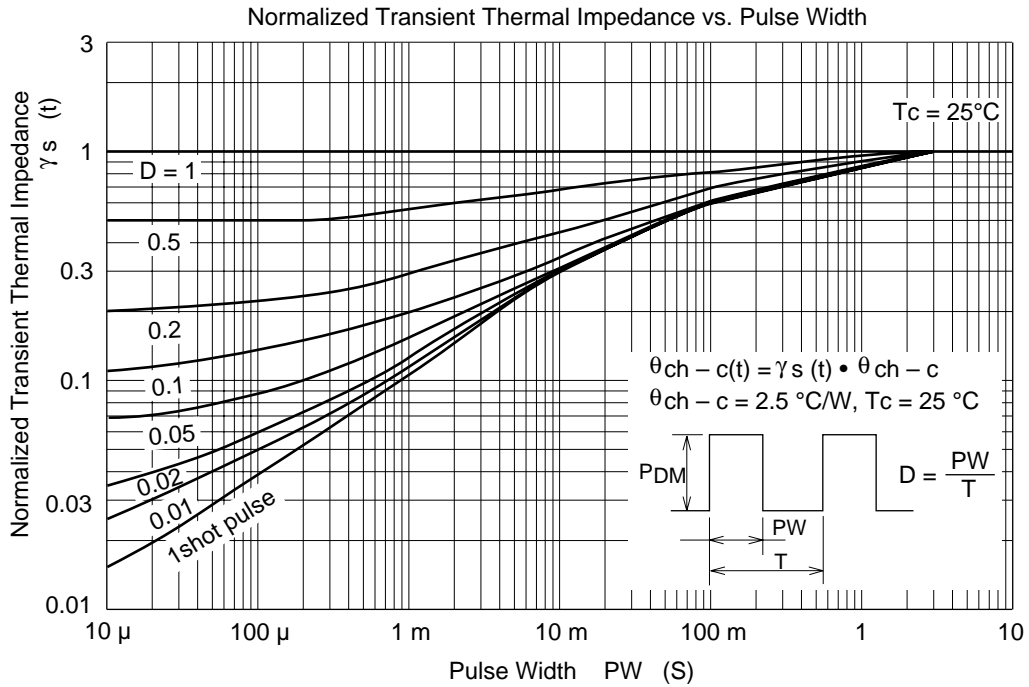
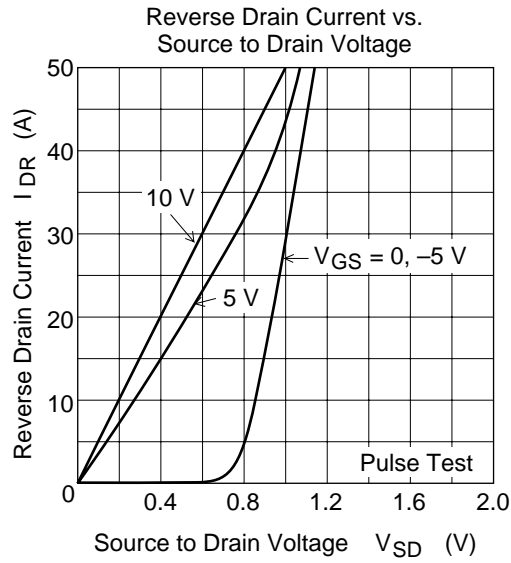
Note: 3. Pulse test

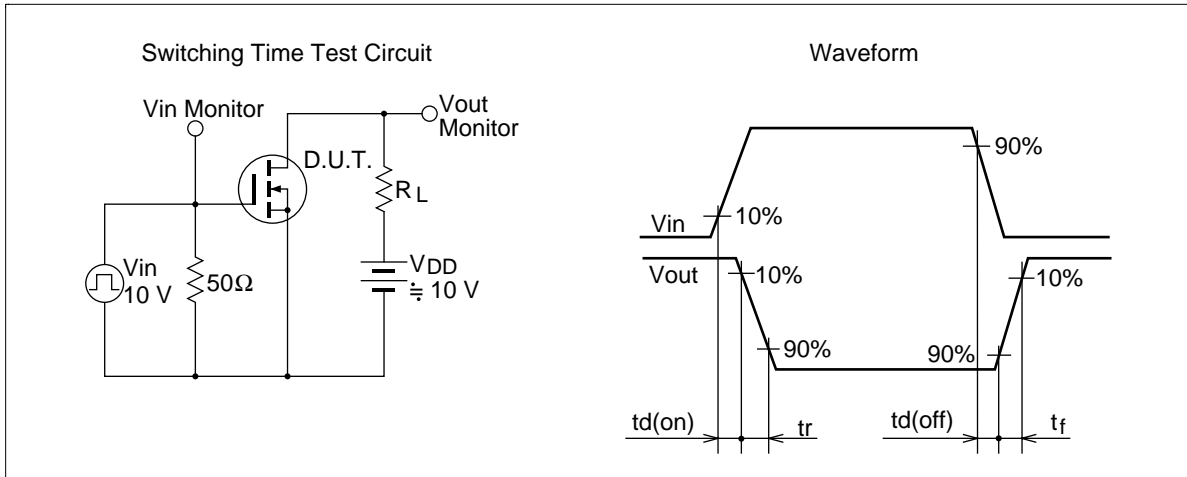
Main Characteristics







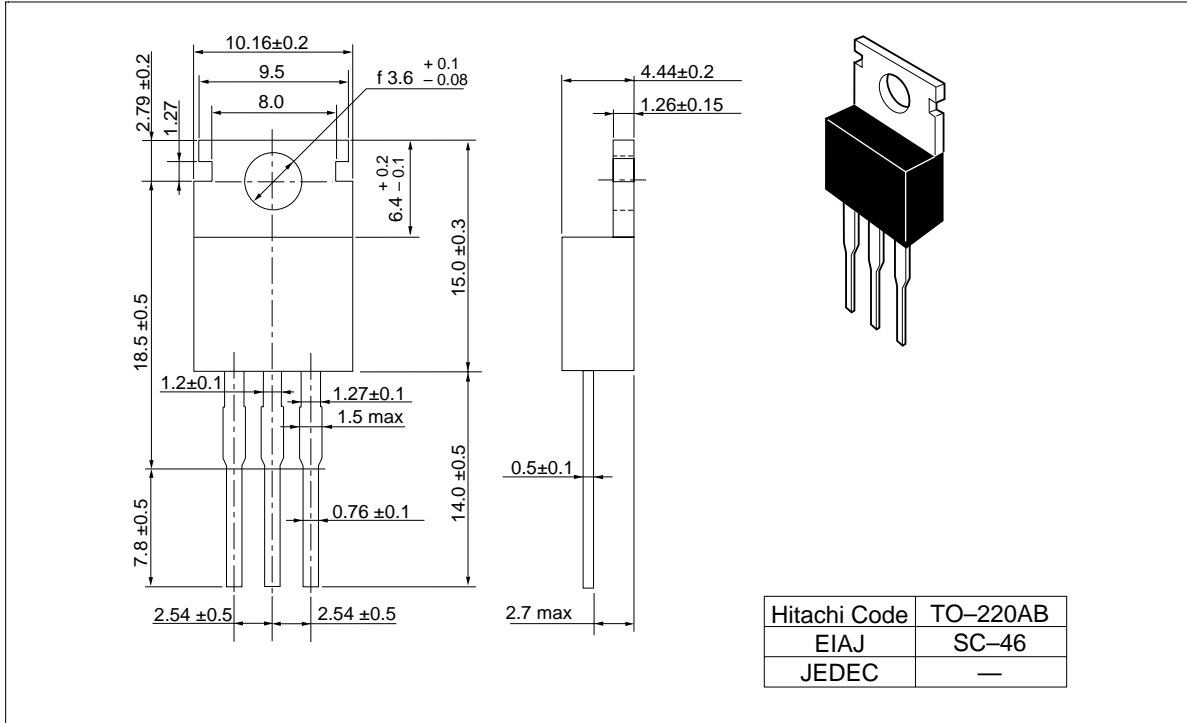




# 2SK3080

## Package Dimensions

Unit: mm





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